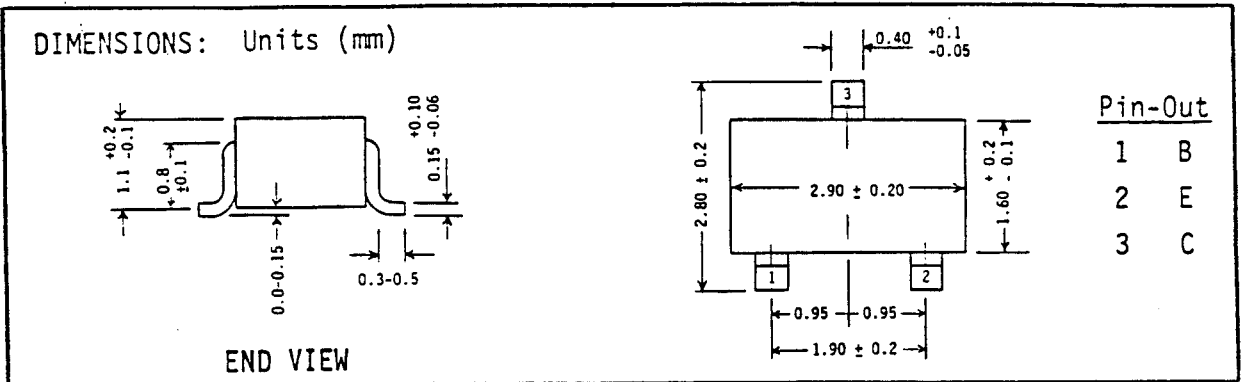


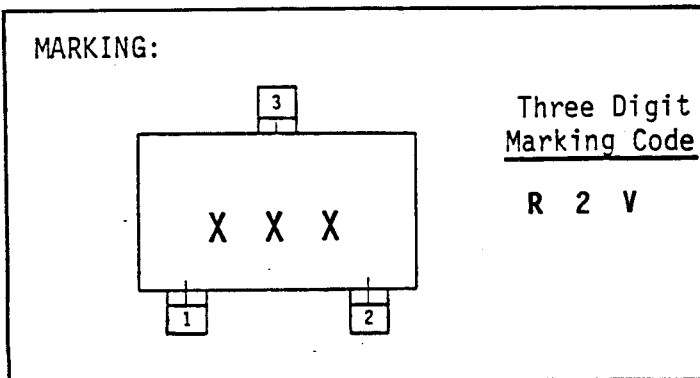
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SUBJECT		
SOT-23 TRANSISTOR, PNP, SILICON		

ABSOLUTE MAXIMUM RATINGS: (Ta = 25°C)

Collector-Base Voltage	V _{CB0}	30 V
Collector-Emitter Voltage	V _{CE0}	30 V
Emitter-Base Voltage	V _{EB0}	10 V
Collector Current	I _C	500 mA
Power Dissipation-Free Air	P _D	200 mW
Power Dissipation-Ceramic Substrate	P _D	350 mW
Operating and Storage Junction Temperature	T _J , T _{stg}	-55 to 150 °C
Solder Temperature (10 seconds)		260 °C



THE JAPANESE STYLE SC-59 PACKAGE



PACKAGING:

_____	BULK, 500 per BAG
_____	MAGAZINES OF 50 EACH
_____	8mm T&R, T-146 3K/REEL
_____	8mm T&R, T-147 3K/REEL
_____	8mm T&R, T-24610K/REEL
_____	8mm T&R, T-24710K/REEL

REMARKS: PROCESS: B-25 Thermal Resistance R_{θJA} 625 °C/Watt
FREE AIR, T_A = 25°C

ROHM ELECTRONICS
3034 Owen Drive, Antioch, TN 37013
TEL: (615) 641-2020 FAX: (615) 641-2022

APPROVAL

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DESIGN

10/12/87

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		January 14, 1987	

TRANSISTOR, PNP ,SILICON	SOT-23
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ELECTRICAL CHARACTERISTICS: (Ta = 25°C Unless Otherwise Specified)

PARAMETER	TEST CONDITIONS	MIN	TYP	MAX	UNIT
BVCES	IC = 100 uA	30			V
ICBO	VCB = 30 V		1.0	100	nA
IEBO	VEB = 10 V		1.0	100	nA
hFE	IC = 10 mA, VCE = 5 V	10,000			
hFE	IC = 100 mA, VCE = 5 V	20,000			
VCE(SAT)	IC = 100 mA, IB = 100 uA			1.5	V
VBE(ON)	IC = 100 mA, VCE = 5 V			2.0	V
fT	IC = 100 mA, VCE = 5 V, f = 100MHz	125			MHz
Cob	VCB = 10 V, IE = 0, f = 100KHz		4.0		pF
hfe	IC = 10 mA, VCE = 5 V, f = 1.0KHz		35,000		
NF	IC = 1.0 mA, VCE = 5 V, Rs = 100KΩ f = 1.0 KHz		2.0		dB

R-Ohm Corporation P.O. Box 19515 Irvine, California 92713		APPROVAL <i>[Signature]</i> 10/12/89	CHECK ✓	DESIGN
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